From: 8064986673 To: USPTO Page: 10/13 Date: 2005/10/12 下午 05:25:00

Appl. No. 10/605,833 Amdt. dated October 12, 2005 Reply to Office action of July 13, 2005

## REMARKS/ARGUMENTS

1. Rejection of claims 1, 7, 10-13, and 21 under 35 U.S.C. 103(a):

Claims 1, 7, 10-13, and 21 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chiyo et al. (US 6,100,545) in view of Yamazaki et al. (US 2003/0062519).

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## Response:

Claim 1 has been amended to overcome this rejection. Claim 1 now contains the limitations "wherein each of the first and second reaction layers is formed to enhance an adhesion provided by the transparent adhesive layer". Neither Chiyo et al nor Yamazaki teach this limitation. The examiner states that Chiyo et al teach a first reaction layer (Ti layer) 2 and a second reaction layer (Buffer layer) 3. However, Chiyo et al do not teach that the first and second reaction layers are formed to enhance an adhesion provided by a transparent adhesive layer since no transparent adhesive layer is taught.

Furthermore, Yamazaki only teaches that a stress relaxing film is interposed between two adjacent layers of two or more passivation films for easing stress (paragraph 0035). Yamazaki does not teach that first and second reaction layers are formed to enhance an adhesion provided by a transparent adhesive layer. Therefore, the amended claim 1 is patentably distinct with respect to the cited prior art.

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Claims 9-21 are amended to correct informalities. No new matter has been added through any of the amendments.

Regarding claim 13, neither Chiyo et al nor Yamazaki et al teach that the second reaction layer comprises at least one material selected from a material group consisting of SiNx, Ti, and Cr.

From: 8064986673 To: USPTO Page: 11/13 Date: 2005/10/12 下午 05:25:01

Appl. No. 10/605,833 Amdt. dated October 12, 2005 Reply to Office action of July 13, 2005

The examiner states that in Fig.18 and in column 2, lines 27-35, Chiyo et al teach a second reaction layer (3) comprising a material selected from a group consisting of SiNx, Ti, and Cr. However, column 2, lines 27-35 only mentions that a buffer layer formed between the Si substrate and an AlGalnN semiconductor layer comprises Ti. From comparing this description to Figure 18, this buffer layer refers to the Ti layer 2, and not to the buffer layer 3. Furthermore, from looking at column 10, lines 36-39, it is clear that the buffer layer 3 comprises Al<sub>0.9</sub>Ga<sub>0.1</sub>N, and does not comprise SiNx, Ti, or Cr. Therefore, since Chiyo et al. does not teach that the second reaction layer comprises at least one material selected from a material group consisting of SiNx, Ti, and Cr, claim 13 is patentable over the combination of Chiyo et al and Yamazaki et al. Furthermore, claims 7, 10-13, and 21 are dependent on claim 1 and should be allowed if claim 1 is allowed. Reconsideration of claims 1, 7, 10-13, and 21 is respectfully requested.

2. Rejection of claims 2-6 and 14-20 under 35 U.S.C. 103(a):

Claims 2-6 and 14-20 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chiyo et al. (US 6,100,545) in view of Yamazaki et al. (US 2003/0062519) and in further view of Uemura et al. (US 2001/0028062).

## 20 Response:

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Claims 2-6 and 14-20 are dependent on claim 1 and should be allowed if claim 1 is allowed. Reconsideration of claims 2-6 and 14-20 is respectfully requested.

3. Rejection of claims 8, 9, and 22 under 35 U.S.C. 103(a):

Claims 8, 9, and 22 are rejected under 35 U.S.C. 103(a) as being unpatentable over Chiyo et al. (US 6,100,545) in view of Yamazaki et al. (US 2003/0062519) and in further view of Sheu (US 2002/0179914) and Schetzina (US 5,670,798).

From: 8064986673 To: USPTO Page: 12/13 Date: 2005/10/12 下午 05:25:01

Appl. No. 10/605,833 Amdt. dated October 12, 2005 Reply to Office action of July 13, 2005

## Response:

Claims 8, 9, and 22 are dependent on claim 1 and should be allowed if claim 1 is allowed. Reconsideration of claims 8, 9, and 22 is respectfully requested.

5 4. Introduction to new claims 23-25:

New claim 23 is a duplicate of claim 12, and is dependent on claim 13. None of the cited prior art references teach or suggest that the second reaction layer contains SiNx, Ti, or Cr and that the transparent adhesive layer comprises PI, BCB, or PFCB.

New claim 24 is based on claim 12, but specifies that the first reaction layer comprises SiNx or Cr, and not including the choice of Ti. Similarly, new claim 25 is based on claim 11, but limits the transparent adhesive layer to comprising PFCB.

No new matter is added through any of the new claims 23-25 and acceptance of new claims 23-25 is respectfully requested.

In view of the above arguments in favor of patentability, the applicant respectfully requests that a timely Notice of Allowance be issued in this case.

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From: 8064986673

To: USPTO

Page: 13/13

Date: 2005/10/12 下午 05:25:01

Appl. No. 10/605,833 Amdt. dated October 12, 2005 Reply to Office action of July 13, 2005

Sincerely yours,

Wenton Han

Date: Oct. 12, 2005

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